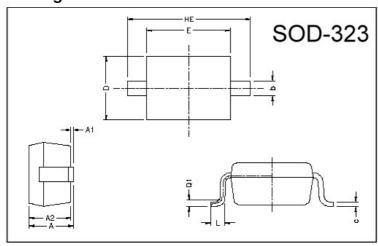
# GDMBD2004

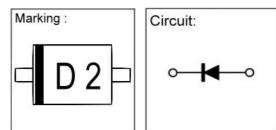
## SURFACE MOUNT, SWITCHING DIODE **VOLTAGE 300V, CURRENT 0.225A**

#### **Description**

The GDMBD2004 is designed for ultra high speed switching.

## **Package Dimensions**





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.	NEF.	Min.	Max.
Α	0.85	1.05			
A1	0	0.10	L	0.20	0.40
A2	0.80	1.00	b	0.25	0.40
D	1.15	1.45	С	0.10	0.18
Е	1.60	1.80			
HE	2.30	2.70	Q1	0.15 BSC.	

### **Absolute Maximum Ratings** (At TA = 25°C unless otherwise specified)

Parameter	Symbol	Ratings	Unit	
Repetitive Peak Reverse Voltage	VRRM	300	V	
Continuous reverse voltage	VR(VRWM)	240	V	
RMS Reverse Voltage	VR(RMS)	170	V	
Forward Continuous Current	lғм	225	mA	
Non-Repetitive Peak Forward surge Current @Tp =1.0us	l=a	4	٨	
@Tp=1.0s	IFSM	1	А	
Typical Junction Capacitance between Terminal (Note1)	Сл	5.0	pF	
Max. Reverse Recovery Time (Note2)	TRR	50	nSec	
Power Dissipation	PD	350	mW	
Thermal Resistance Junction to Ambient Air	Reja	357	°C/W	
Operation and Storage Temperature Range	TJ, TSTG	-65 ~ +150	$^{\circ}\! \mathbb{C}$	

#### Electrical Characteristics (At TA = 25°C unless otherwise noted)

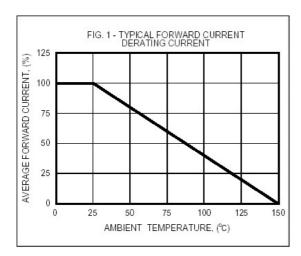
Characteristics	Symbol	Min.	Max.	Unit	Test Conditions			
Reverse Breakdown Voltage	BVR	300	-	V	In=100uA			
			0.85	V	IF=20mA			
Forward Voltage	VF	-	1	V	IF=100mA			
		-	1.25	V	IF=225mA			
Reverse Current	IR	-	100	nA	VR=240V, Ta=25°C			
neverse Guiterii	IK		100	uA	VR=240V, Ta=150°C			

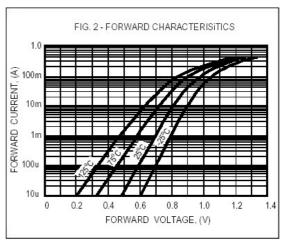
Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 0 volts.

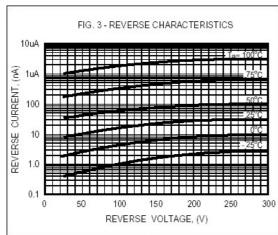
- 2. Measured at applied forward current of 30mA, reverse current of 30mA,  $R_L$ =100 $\Omega$  and recovery to  $I_{RR}$ =-3mA.
- 3. ESD sensitive product handling required.

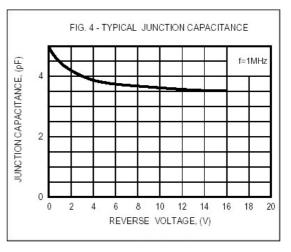
GDMBD2004 www.DataSheet4b.com

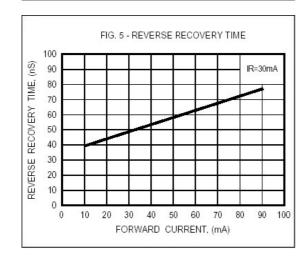
#### **Characteristics Curve**

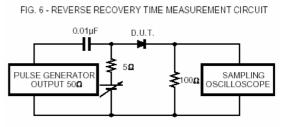












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